

Innovations Embedded





**Selection Guide** 

The demands for extended battery operation, greater reliability and increased features are driving the designs of mobile phones, notebook computers, video cameras, navigation systems and game controllers to use smaller, higher performance components.

Ultra-small, hall effect, non-contact switches from ROHM Electronics can simplify and enhance your designs while offering the benefits of high-reliability and low power consumption. These high performance devices are the ideal choice for a range of switch applications:

- Portable phone or PDA in or out of its carrying case
- Slide-open or closed on cell phone or camera
- Flip phone or laptop cover open or closed
- Cell phone or tablet PC screen
   orientation
- Track wheel position on MP3 players, toys and games

(×10 display)

ROHM's advanced packaging options include the industry's smallest BGA chipscale package as well as low-profile, ultra-small SMT package.





### Designed for Performance and Reliability

	<ul> <li>Single-chip IC with built-in Hall element</li> <li>Eliminates wire-bonding reliability problems</li> </ul>
LOW	<ul> <li>Low current consumption with CMOS output</li> <li>Eliminates the need for external pull-up resistor</li> </ul>
In.	<ul><li>Intermittent operation for longer battery life</li><li>Pulsed detection reduces average power consumption</li></ul>
High sensitivity	<ul> <li>High detection sensitivity</li> <li>Integrated dynamic offset cancellation yields high performance in small package</li> </ul>
-40℃ +85℃	<ul> <li>-40C to +85C Operating Range</li> <li>Assures worry-free operation under extreme conditions</li> </ul>
8 kv	<ul> <li>8 kV ESD Withstand</li> <li>High reliability in real-world conditions</li> </ul>

## Selections for Every Application

#### Unipolar Operation

These devices detect the presence of either a N-pole or S-pole magnetic field of sufficient strength, but not both. They offer the lowest power consumption. The output switches state when the magnetic field is removed

#### **Omnipolar Operation**

These devices detect the presence of either a N-pole or S-pole magnetic field eliminating the need to orient the magnet for detection. This can simplify the manufacturing process. The trade-off is slightly higher power consumption

#### Polarity Discrimination

These devices feature dual outputs, one switches state in the presence of a N-pole magnetic field, the other in the presence of a S-pole. Both outputs revert to the alternative state when the field is removed. These devices are used to detect the combination of operation (open/closed) and position (front/back)

#### **Bipolar Operation**

• These devices change output state whenever a magnetic field of the opposite polarity is detected. The output remains fixed in its current state if no magnetic field is present. Applications are in jog wheel or track ball movement detection. They have higher sampling rates and power consumption

# Omnipolar Detection

The application of bipolar detection Hall ICs simplifies product design, assembly and maintenance. These devices can detect both S-pole and N-pole magnetic fields. Magnet management is simplified since the Hall IC will operate properly regardless of magnet orientation.



## Polarity Discrimination

Omnipolar detection Hall ICs with built-in polarity discrimination add the capability of both detecting the position and the orientation of the magnet — important in applications where the display orientation of the device can be rotated.





### Unipolar Detection

For the most cost-effective and lowest power implementation, unipolar detection Hall ICs provide the answer. The trade off comes from the need to assure proper magnet orientation in the production process.



# Bipolar (Latching) Detection

Bipolar (latching) Hall ICs add the capability of detecting the dynamic movement of devices like jog wheels or track balls. Two of these devices are typically used to detect CW and CCW movement.





Omnipolar Detection Hall ICs Detects both S-pole and N-pole magnetic fields and turns the output ON (active Low).									
Part Number	Supply Voltage (V)	Operating Magnetic Flux Density (mT)	Hysteresis (mT)	Pulse Driving Cycle (mS)	Current Consumption (Typ.) (µA)	Output	Package		
BU52001GUL	2.40 - 3.3	±3.7	0.8	50	8.0	CMOS	VCSP50L1		
BU52011HFV	1.65 - 3.3	±3.0	0.9	50	5.0	CMOS	HVS0F5		
BU52015GUL*	1.65 - 3.3	±3.0	0.9	50	5.0	CMOS	VCSP50L1		
*The BU52015GUL features reverse output									
BU52001GUL	S N		1 OUT Sensit			中 氏 MOS			
BU52011HFV	S N	Ultra Small	1 OUT Sensit			中 MOS			
BU52015GUL	SN		2 DUAL Sensit		<b>8</b> kV +85°c	中 E E MOS			

Polarity Discrimination Hall ICs Features two outputs to discriminate between N-pole and S-pole detection.							
Part Number	Supply Voltage (V)	Operating Magnetic Flux Density (mT)	Hysteresis (mT)	Pulse Driving Cycle (mS)	Current Consumption (Typ.) (µA)	Output	Package
BU52004GUL	2.40 - 3.3	±3.7	0.8	50	8.0	CMOS	VCSP50L1
BU52014HFV	1.65 - 3.3	±3.0	0.9	50	5.0	CMOS	HVSOF5
BU52004GUL	S N		<b>S N</b> OUT OUT sensit	h III	8 KV 40c +85c	<b>中</b> M0S	distrimination
BU52014HFV	S N	Ultra Small	<b>SN</b> OUT OUT sensit		8/kV +85°c	中 <b>C</b> 中MOS	





Unipolar Detection Hall ICs Detects either N-pole or S-pole but not both.								
Part Number	Supply Voltage (V)	Operating Magnetic Flux Density (mT)	Hysteresis (mT)	Pulse Driving Cycle (mS)	Current Consumption (Typ.) (µA)	Output	Package	
BU52002GUL	2.40 - 3.3	3.7	0.8	50	6.5	CMOS	VCSP50L1	
BU52003GUL	2.40 - 3.3	-3.7	0.8	50	6.5	CMOS	VCSP50L1	
BU52012HFV	1.65 - 3.3	3.0	0.9	50	3.5	CMOS	HVSOF5	
BU52013HFV	1.65 - 3.3	-3.0	0.9	50	3.5	CMOS	HVSOF5	
BU52002GUL	S		1 OUT Sensi	gh Mity <b>Fr</b>	<b>8</b> / KV +85°c	中 <b>C</b> 中MOS		
BU52003GUL	<b>N</b> ∭		1 OUT sensi		8/kV +85°c	中 <b>C</b> 中MOS		
BU52012HFV	S	litra mall POWER SUPPLY	1 OUT Sensi	n n n n n n n n n n n n n n n n n n n		中 <b>C</b> 中MOS		
BU52013GUL	N	Iltra mall POWER SUPPLY	1 OUT Sensi	gh Intr		中 <b>C</b> 中 MOS		

Bipolar (Latching) Detection Hall ICs Features two outputs to discriminate between N-pole and S-pole detection.								
Part Number	Supply Voltage (V)	Operating Magnetic Flux Density (mT)	Hysteresis (mT)	Pulse Driving Cycle (mS)	Current Consumption (Typ.) (µA)	Output	Package	
BU52040HFV	1.65 - 3.3	±3.0	±6.0	500	300	CMOS	HVSOF5	
BU52013GUL	S N	Ultra Small Power Supply	SN OUT OUT sensit	gh Inte	8/kV -40°c +85°c	中 <b>C</b> 中MOS		





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